

WHAT IS CLAIMED IS:

1. A semiconductor light emitting device, comprising:
 - a semiconductor substrate;
 - a stacked semiconductor structure formed on the semiconductor substrate;
 - a striped ridge structure; and
 - a semiconductor current confinement layer provided on a side surface of the striped ridge structure;wherein the stacked semiconductor structure includes a first semiconductor clad layer, a semiconductor active layer, a second semiconductor clad layer, and a semiconductor etching stop layer;
- wherein the striped ridge structure includes a third semiconductor clad layer, a semiconductor intermediate layer, and a semiconductor cap layer;
- wherein the striped ridge structure is provided on the semiconductor etching stop layer; and
- wherein an interface between the semiconductor current confinement layer and the semiconductor etching stop layer and an interface between the semiconductor current confinement layer and the striped ridge structure each have a content of impurities of less than $1 \times 10^{17}/\text{cm}^3$.

2. A semiconductor light emitting device according to claim 1, wherein the impurities are carbon-based impurities.

3. A semiconductor light emitting device according to claim 1, wherein the impurities are oxygen-based impurities.

4. A semiconductor light emitting device according to claim 1, wherein the impurities are carbon-based impurities and oxygen-based impurities.

5. A method for producing a semiconductor light emitting device, comprising the steps of:

forming a first stacked semiconductor structure on a semiconductor substrate, the first stacked semiconductor structure including a first semiconductor clad layer, a semiconductor active layer, a second semiconductor clad layer and a semiconductor etching stop layer;

forming a second stacked semiconductor structure on the semiconductor etching stop layer, the second stacked semiconductor structure including a third semiconductor clad layer, a semiconductor intermediate layer and a

semiconductor cap layer;

forming an oxide layer on the second stacked semiconductor structure;

processing at least the second stacked semiconductor structure into a striped ridge structure;

washing the first stacked semiconductor structure and the striped ridge structure with a washing liquid having a prescribed resistivity; and

forming a semiconductor current confinement layer on a side surface of the striped ridge structure.

6. A method for producing a semiconductor light emitting device according to claim 5, wherein the prescribed resistivity is higher than 1 M Ω m.

7. A method for producing a semiconductor light emitting device according to claim 5, wherein the washing liquid is pure water.

8. A method for producing a semiconductor light emitting device according to claim 7, wherein the prescribed resistivity is higher than 1 M Ω m.